



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Harry S. Luan, et al. Serial No.: 10/777,560 Filed: February 11, 2004 For: STACKABLE RESISTIVE CROSS-POINT MEMORY WITH SCHOTTKY DIODE ISOLATION	Examiner: Tinh Nguyen Art Unit: 2818 INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR §1.97 and §1.98
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Assistant Commissioner for Patents
 Washington, D.C. 20231

Sir:

The references cited on attached form PTO-1449 are being called to the attention of the Examiner. Copies of the references are enclosed. It is respectfully requested that the cited information be expressly considered during the prosecution of this application, and the references be made of record therein and appear among the "references cited" on any patent to issue there from.

As provided for by 37 CFR 1.97(g) and (h), no inference should be made that the information and references cited are prior art merely because they are in this statement and no representation is being made that a search has been conducted or that this statement encompasses all the possible relevant information.

The Commissioner is authorized to deduct such fee from the undersigned's Deposit Account No. 50-1229. Please deduct any additional fees from, or credit any overpayment to, the above-noted Deposit Account.

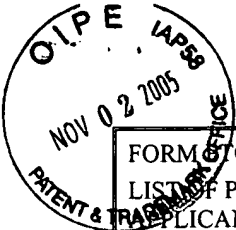
Respectfully submitted,

Truong T. Dinh
 Reg. No. 40,993

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DINH & ASSOCIATES 2506 Ash Street Palo Alto, California 94306 Tel: (650) 289-0600 Fax: (650) 289-0700	I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 By: On: <u>October 26, 2005</u>
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FORM PTO-1449 (Modified)	Attorney Docket No.: 108-18.1	Application No.: 10/777,560
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	Applicant: Harry S. Luan, et al.	
	Filing Date: February 11, 2004	Group:

Reference Designation	U.S. PATENT DOCUMENTS	Page 1
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Examiner Initial	Document No.	Date	Name	Class	Sub-class	Filing Date (If Appropriate)
___ AA	6,204,139	3/20/01	Liu et al	438	385	
___ AB	6,531,371	3/11/03	Hsu et al	438	385	
___ AC						
___ AD						
___ AE						
___ AF						
___ AG						
___ AH						
___ AI						
___ AJ						
___ AK						
___ AL						
___ AM						
___ AN						
___ AO						

FOREIGN PATENT DOCUMENTS

Document No.	Date	Country	Class	Sub-class	Translation (Yes/No)

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)
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___ AP	Zhuang et al., "Novell Colossal Magnetoresistive Thin Film Nonvolatile Resistance Random Access Memory (RRAM)," IEEE 2002.
___ AQ	Liu et al., "A New Concept for Non-Volatile Memory: The Electric Pulse Induced Resistive Change Effect in Colossal Magnetoresistive Thin Films,"
___ AR	Liu et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films," American Institute of Physics, 2000, pg. 2749-2751.
___ AS	
___ AT	
___ AU	
___ AV	
___ AW	
___ AX	

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.